



Better Performance for Radio Communication Network

MITSUBISHI SiRF Devices are Key parts of RF Power Amplifications for various kind of Mobile Radio, Professional Mobile Radios, Amateur Radios, Car Phones for GSM/AMPS and TELEMATICS for automotive. MITSUBISHI SiRF Devices strongly support for Radio communication network.

High Output Power Si MOS FET (Discrete)

30MHz Band

Type Number	Structure	Max.ratings		Vdd (V)	f (MHz)	Pin (W)	Po(min) (W)	nd(min) (%)	Package outline
		VDSS (V)	Pch (W)						
RDO0HHS1	Si,MOS	30	3.1	12.5	30	0.004	0.3	55	SOT-89
RDO6HHF1	Si,MOS	50	27.8	12.5	30	0.15	6	55	TO-220S
RD16HHF1	Si,MOS	50	56.8	12.5	30	0.4	16	55	TO-220S
RD70HHF1	Si,MOS	50	150	12.5	30	3.5	70	55	Ceramic(Large)
Tc=25°C RD100HHF1	Si,MOS	50	176.5	12.5	30	7	100	55	Ceramic(Large)

175/520 MHz Band

Type Number	Structure	Max.ratings		Vdd (V)	f (MHz)	Pin (W)	Po(min) (W)	nd(min) (%)	Package outline
		VDSS (V)	Pch (W)						
RDO0HVS1	Si,MOS	30	3.1	12.5	175	0.005	0.5	50	SOT-89
RDO1MUS1	Si,MOS	30	3.6	7.2	520	0.03	0.8	50	SOT-89
RDO1MUS2	Si,MOS†	30	3.6	7.2	520	0.03	0.8	50	SOT-89
RDO2MUS1	Si,MOS	30	21.9	7.2	175/520	0.05/0.05	2/2	55/50	SLP
RDO2MUS1B*	Si,MOS	30	21.9	7.2	175/520	0.05/0.05	2/2	55/50	SLP
RDO2MUS2	Si,MOS†	30	21.9	7.2	175/520	0.05/0.05	2/2	55/50	SLP
RDO6HVF1	Si,MOS	50	27.8	12.5	175	0.3	6	60	TO-220S
RDO7MVS1	Si,MOS	30	50	7.2	175/520	0.3/0.7	7/7	55/50	SLP
RDO7MVS1B*	Si,MOS	30	50	7.2	175/520	0.3/0.7	7/7	55/50	SLP
RDO7MVS2	Si,MOS†	30	50	7.2	175/520	0.3/0.7	7/7	55/50	SLP
RDO9MUP2	Si,MOS†	30	83	7.2	520	0.8	8	50	PMM
RD12MVS1	Si,MOS	50	50	7.2	175	1	11.5	55	SLP
RD12MVS1	Si,MOS	50	125	7.2	175	0.5	10	55	PMM
RD15HVF1	Si,MOS	30	48	12.5	175/520	0.6/3	15/15	55/50	TO-220S
RD30HVF1	Si,MOS	30	75	12.5	175	1	30	55	Ceramic(Small)
RD30HUF1	Si,MOS	30	75	12.5	520	3	30	50	Ceramic(Small)
RD70HVF1	Si,MOS	30	150	12.5	175/520	6/10	70/50	55/50	Ceramic(Large)
Tc=25°C RD60HUF1	Si,MOS	30	150	12.5	520	10	60	50	Ceramic(Large)

*: New product † : Gate Protection Diode

900MHz Band

Type Number	Structure	Max.ratings		Vdd (V)	f (MHz)	Pin (W)	Po(min) (W)	nd(min) (%)	Package outline
		VDSS (V)	Pch (W)						
RDO5MMP1	Si,MOS	30	73	7.2	941	0.7	5.5	43	PMM
RD20HMF1	Si,MOS	30	71.4	12.5	900	3	30	50	Ceramic(Small)
Tc=25°C RD45HMF1	Si,MOS	30	125	12.5	900	15	45	45	Ceramic(Large)

High Output Power Si MOS FET Module

66-88MHz Band

Type Number	Max.ratings Vdd(V)	f(MHz)		Vdd (V)	Pin (W)	Po(min) (W)	nd(min) (%)	Package outline
		min	max					
RA07M0608M	9.2	66	88	7.2	0.03	7	45	H46S
RA07H0608M	13.2	68	88	12.5	0.03	7	38	H46S
RA30H0608M	17	66	88	12.5	0.05	30	40	H2S